Personnel

High-*k* Materials for Future IC Technology (2005-2010) and INVENT (2010-2014)

Dr Mircea Modreanu

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Research activities

CVD process development and optical and microstructural characterisation of polysilicon, doped silicon oxides and silicon nitrides and oxynitride thin films used in microelectronics, photonics and microsensors applications.

Biography

Dr. Mircea Modreanu obtained his Master of Science degree in Physics from University of Bucharest, 1993 and Ph.D. degree in Solid State Physics from University of Bucharest, Romania, 2002. Between 1993 and 2002, Dr. Modreanu was working as Senior Researcher at IMT-Bucharest, Romania in development of CVD thin films for microelectronics, photonics and microsystems (microsensors) applications. One of his main areas of expertise is related to optical and microstructural characterisation of thin films (spectroscopic ellipsometry, UV-Vis spectrophotometry, FTIR, Raman and XRD). Since 2002, Dr. Modreanu is working as a Post-Doctoral

Fellow in Tyndall National Institute-UCC, Ireland, being involved in optical metrology and microstructural characterisation of thin films for photonics and microelectronic applications.

Publications

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